



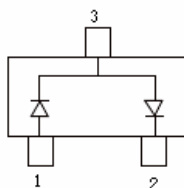
SOT-23 Plastic-Encapsulate Diodes

DAN217 SWITCHING DIODE

FEATURES

- Small surface mounting type
- Two diode elements are connected in series

MARKING: BA1



Maximum Ratings @T_A=25 °C

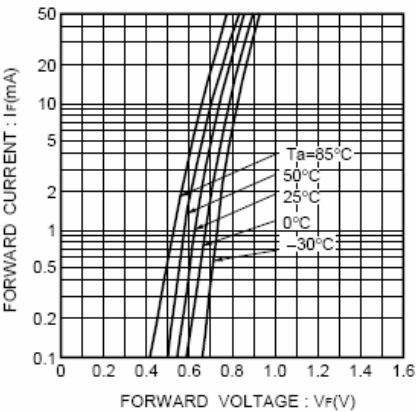
Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	80	V
DC reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300	mA
Average forward current	I _O	100	mA
Surge current (10ms)	I _{FSM}	1	A
Power dissipation	P _D	200	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

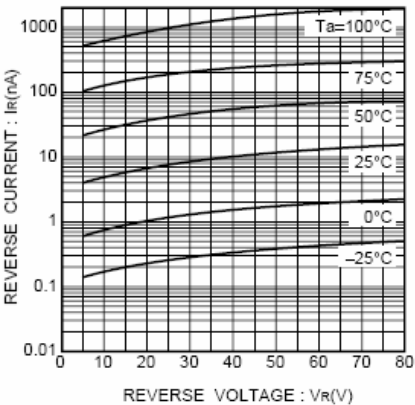
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 100μA	80		V
Reverse voltage leakage current	I _R	V _R =70V		0.1	μA
Forward voltage	V _F	I _F =100mA		1.2	V

Typical Characteristics

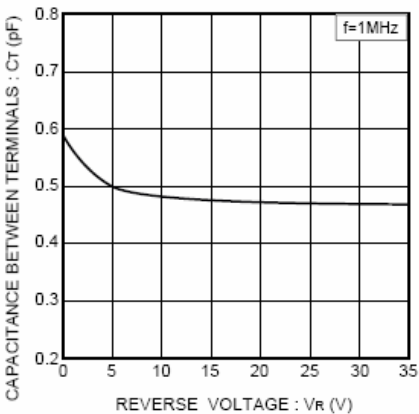
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Forward characteristics



Reverse characteristics



Capacitance between terminals characteristics